



Paper #12 (IDS)

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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	09/943,187
				Filing Date	August 29, 2001
				First Named Inventor	Kristy A. Campbell, et al.
				Art Unit	2822
				Examiner Name	Khanh B. Duong
Sheet	1	of	8	Attorney Docket Number	M4065.0703/P703

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number-Kind Code ² (if known)			
KBD ↓	AA	6,388,324	05/14/2002	Kozicki et al.	
	AB	US 2002/0000666	01/03/2002	Kozicki et al.	
	AC	5,500,532	03/19/1996	Kozicki et al.	
	AD	6,469,364 B1	10/22/2002	Kozicki	
	AE	US 2002/0168820	11/14/2002	Kozicki et al.	

FOREIGN PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	Foreign Patent Document	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Country Code ³ -Number ⁴ -Kind Code ⁵ (if known)			
KBD ↓	BA	WO 97/48032	12/18/1997	Kozicki et al.	
	BB	WO 99/28914	06/10/1999	Kozicki et al.	

Examiner Signature		Date Considered	3/8/03
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*EXAMINER: Initial reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant

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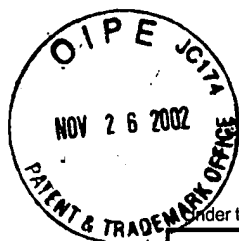
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Sheet	2	of	8	Attorney Docket Number	M4065.0703/P703

OTHER PRIOR ART – NON PATENT LITERATURE DOCUMENTS		
Examiner Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, page(s), volume-issue number(s), publisher, city and/or country where published.
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	CI	Aniya, M., Average electronegativity, medium-range-order, and ionic conductivity in superionic glasses, Solid state Ionics 136-137 (2000) 1085-1089.
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	CR	Bernede, J.C., Switching and silver movements in Ag ₂ Se thin films, Phys. Stat. Sol. (a) 57 (1980) K101-K104.
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Sheet	3	of	8	Attorney Docket Number	M4065.0703/P703

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First Named Inventor	Kristy A. Campbell, et al.
Group Art Unit	2822
Examiner Name	Khanh B. Duong
Attorney Docket Number	M4065.0703/P703

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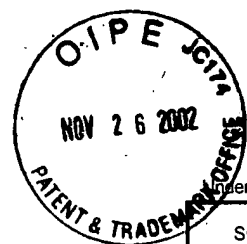
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KBD	CP3	Korkinova, Ts.N.; Andreichin, R.E., Chalcogenide glass polarization and the type of contacts, Non-Cryst. Solids 194 (1996) 256-259.	
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	CV3	Matsushita, T.; Yamagami, T.; Okuda, M., Polarized memory effect observed on Se-SnO2 system, Jap. J. Appl. Phys. 11 (1972) 1657-1662.	
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			Application Number	09/943,187	
			Filing Date	August 29, 2001	
			First Named Inventor	Kristy A. Campbell, et al.	
			Group Art Unit	2822	
			Examiner Name	Khanh B. Duong	
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Examiner Signature		Date Considered	3/8/03
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